

***Semiconductor
Device Fabrication
Using CMP Technology***

Chemical Mechanical Planarizing Technology

MECHANICAL

▶ ***Tiny, solid abrasive particles suspended in a solution***

act like liquid sandpaper to polish the wafer surface.

- Silica
(silicon dioxide or SiO_2)
- Alumina
(aluminum oxide or Al_2O_3)

CHEMICAL

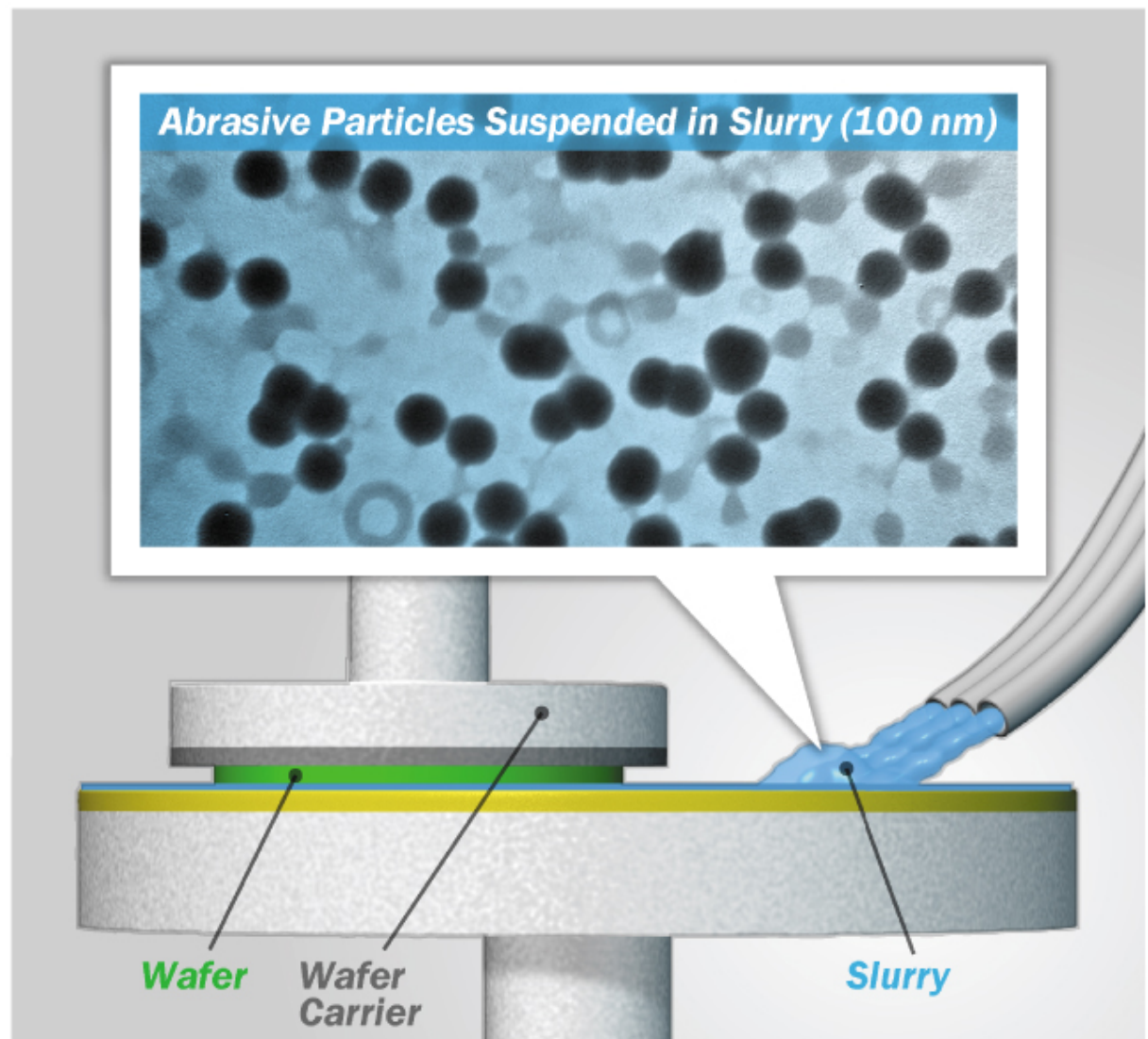
▶ ***Oxidizing agent*** chemically reacts with a metal layer to facilitate its removal.

▶ ***Catalyst*** enhances a chemical (oxidation) reaction.

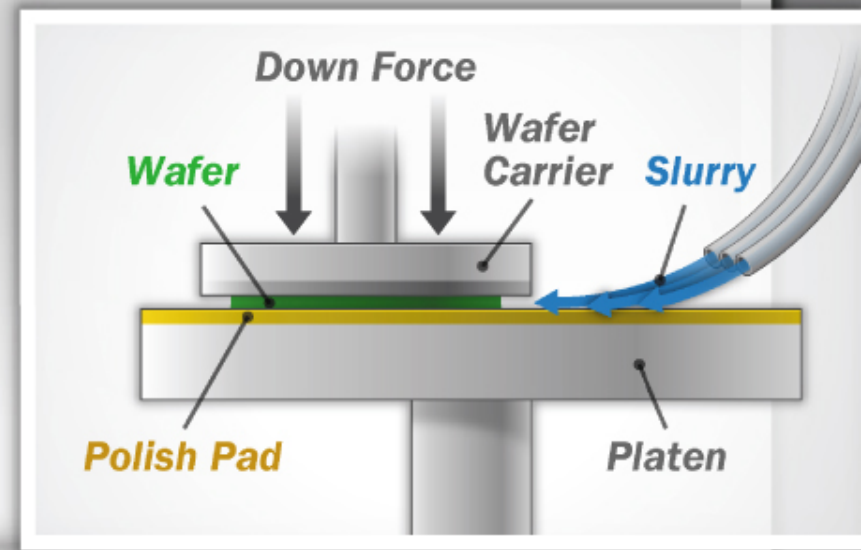
▶ ***Stabilizer (1)*** keeps the oxidizing agent intact until ready for use.

▶ ***Stabilizer (2)*** keeps the abrasive particles suspended in solution until ready for use.

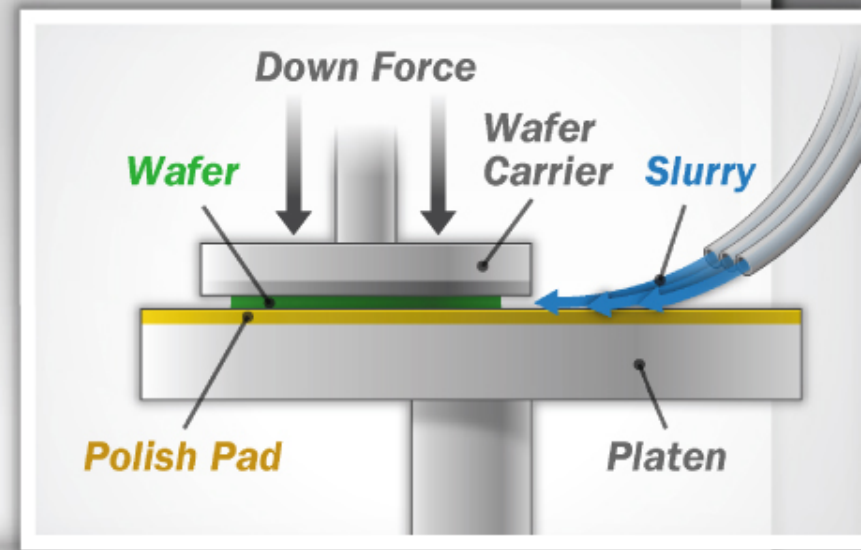
**The
“Mechanical”
Component of
CMP Technology**



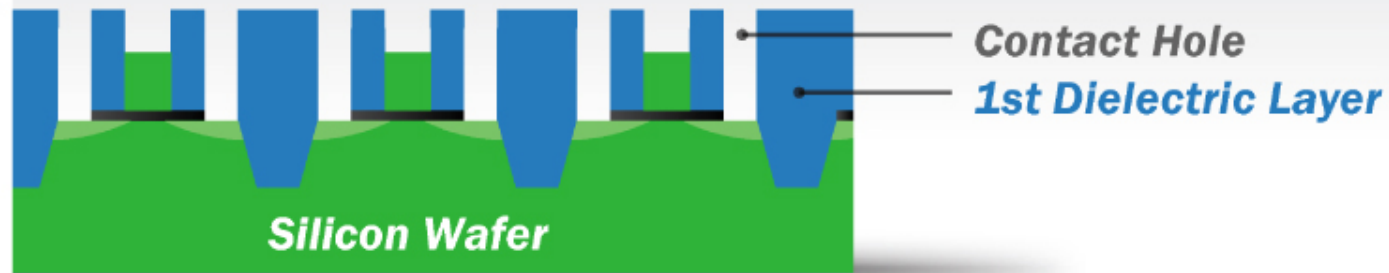
The First Dielectric Layer Is Planarized Using CMP Technology



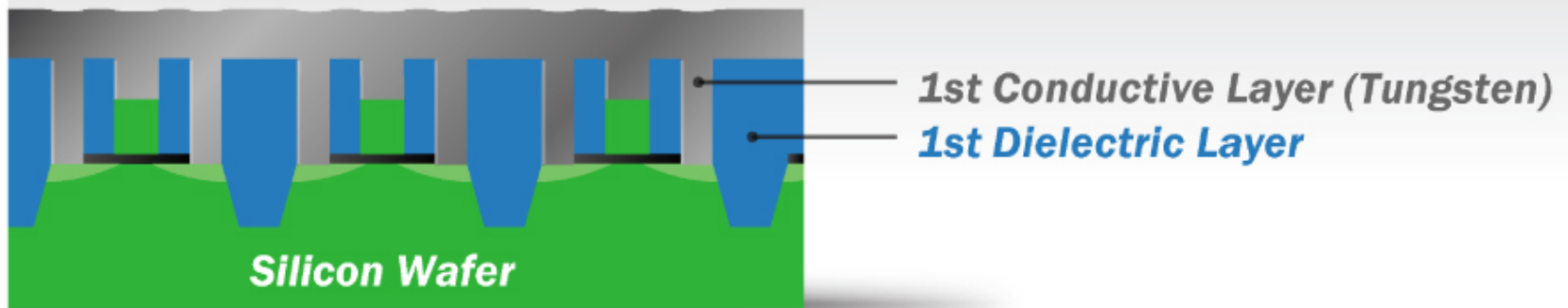
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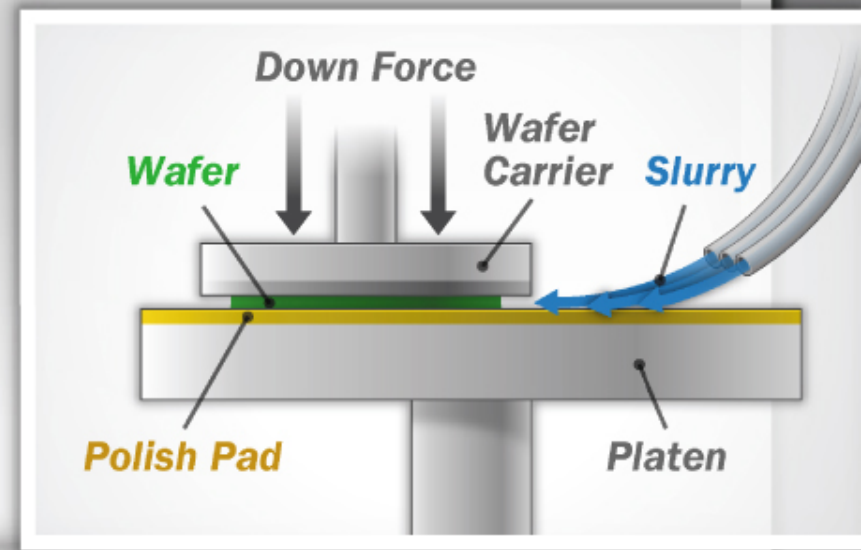
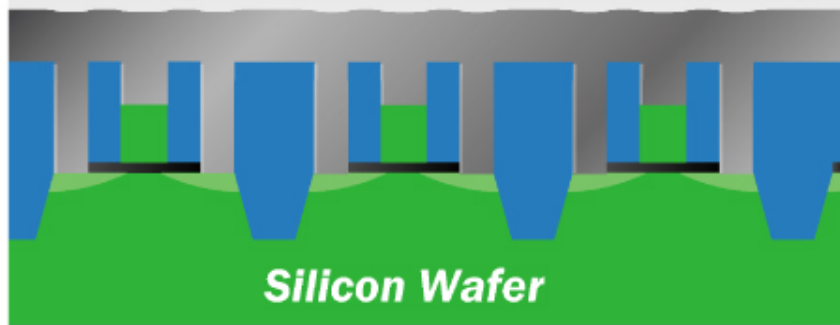
Contact Holes Are Patterned in the First Dielectric Layer



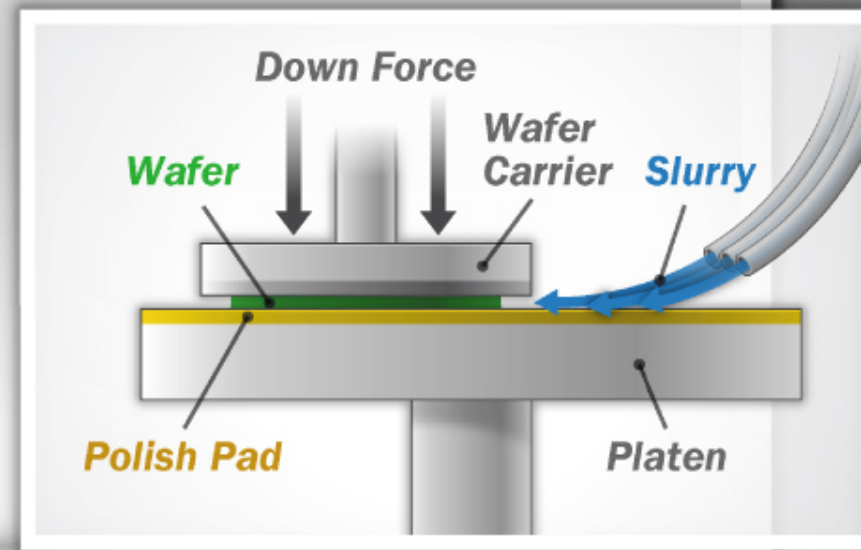
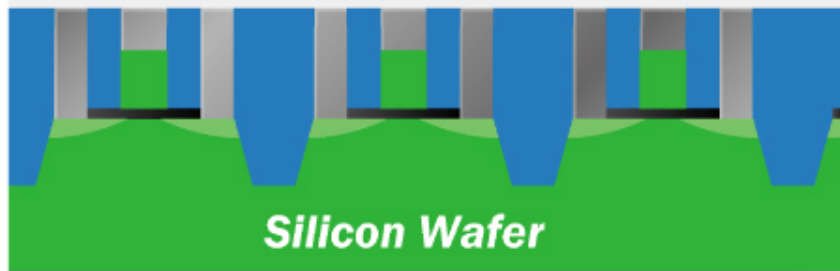
Deposition of the First Conductive Layer (Tungsten)



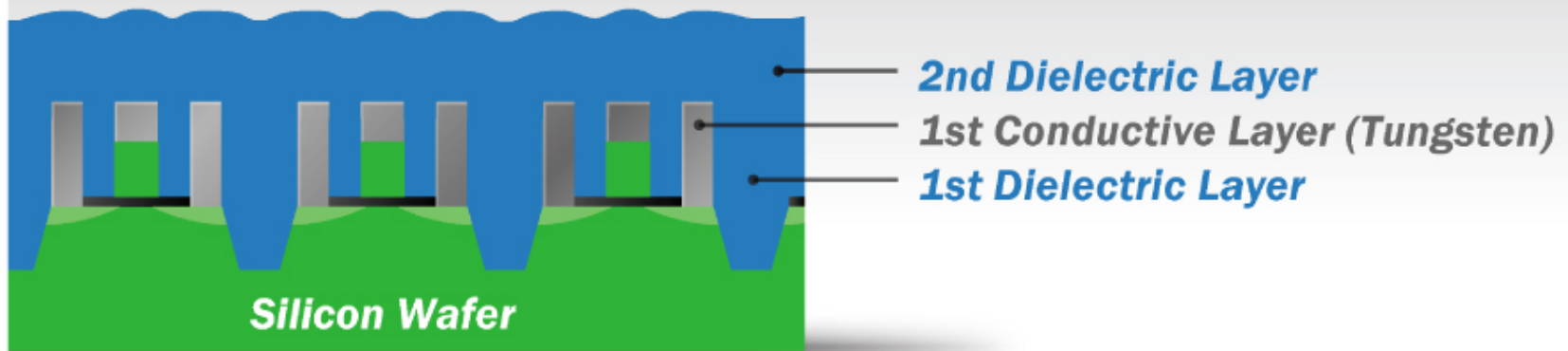
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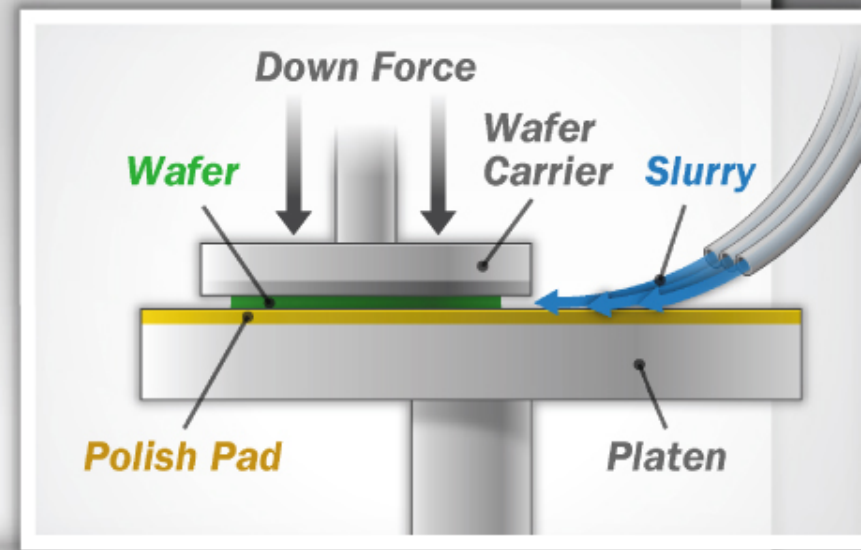
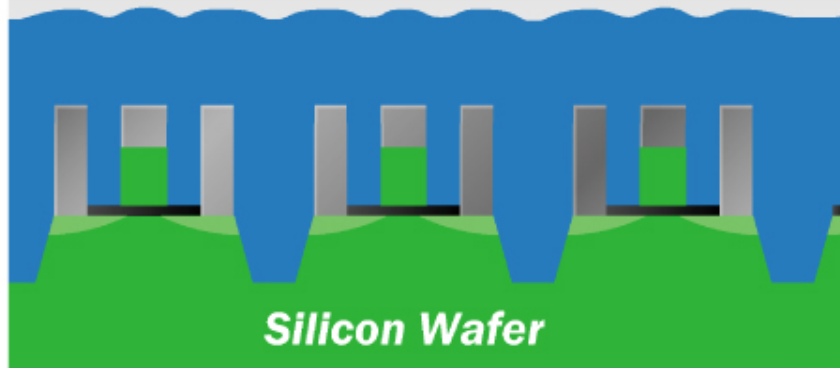
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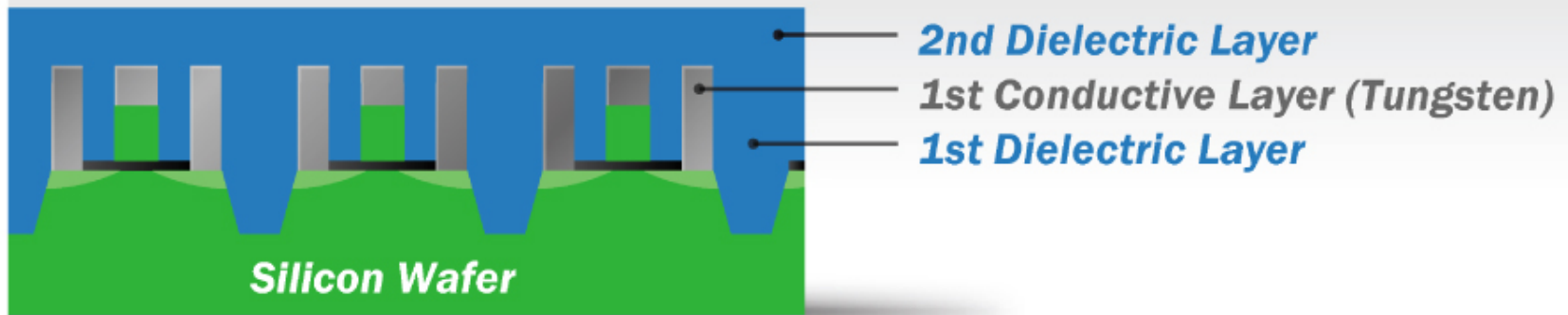
Subsequent Dielectric Layers and Conductive (Metal) Layers Are Planarized Using CMP Technology



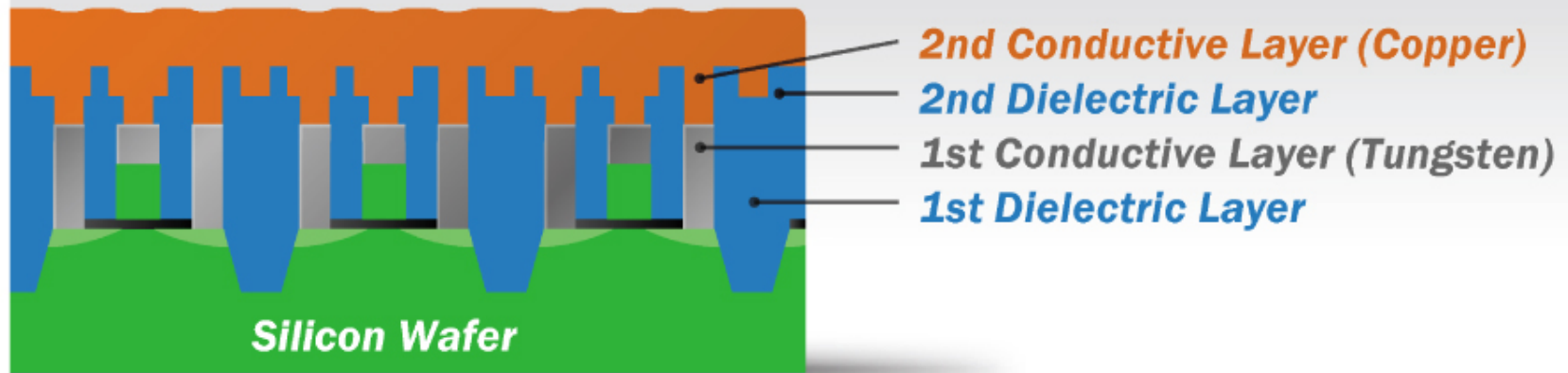
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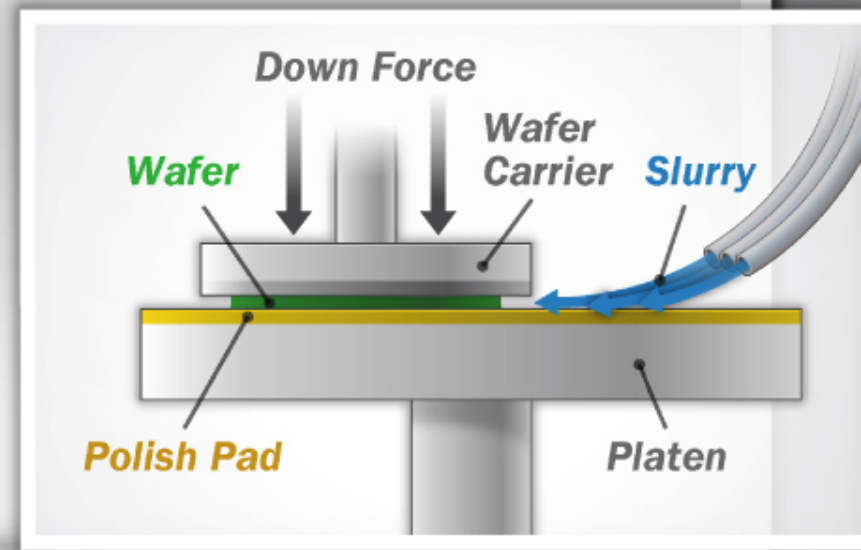
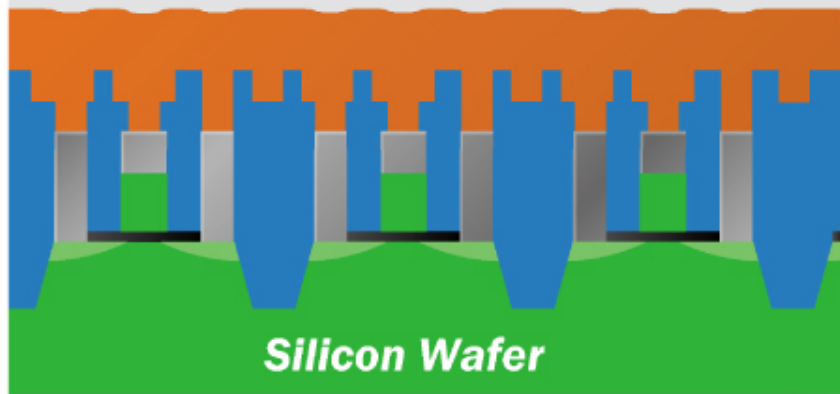
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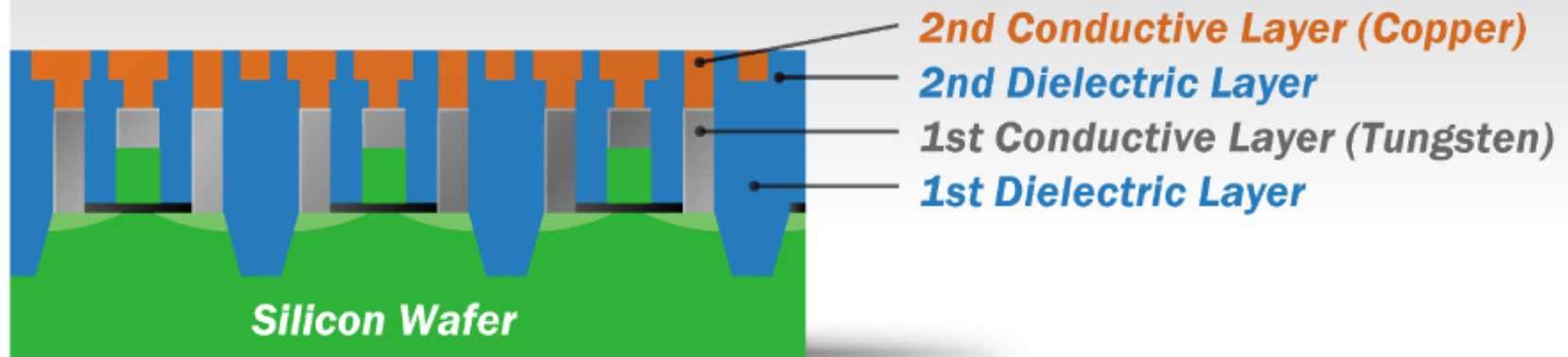
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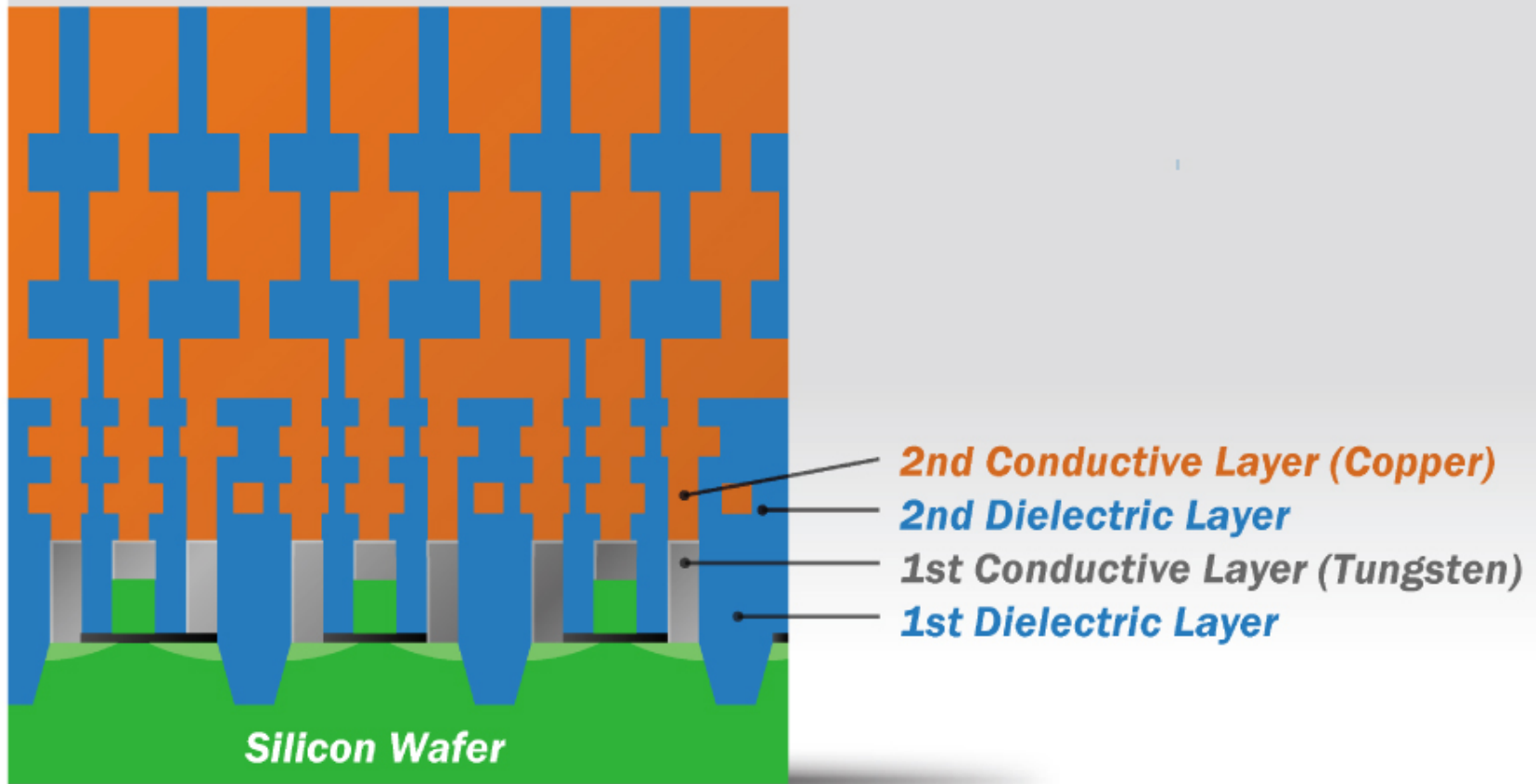
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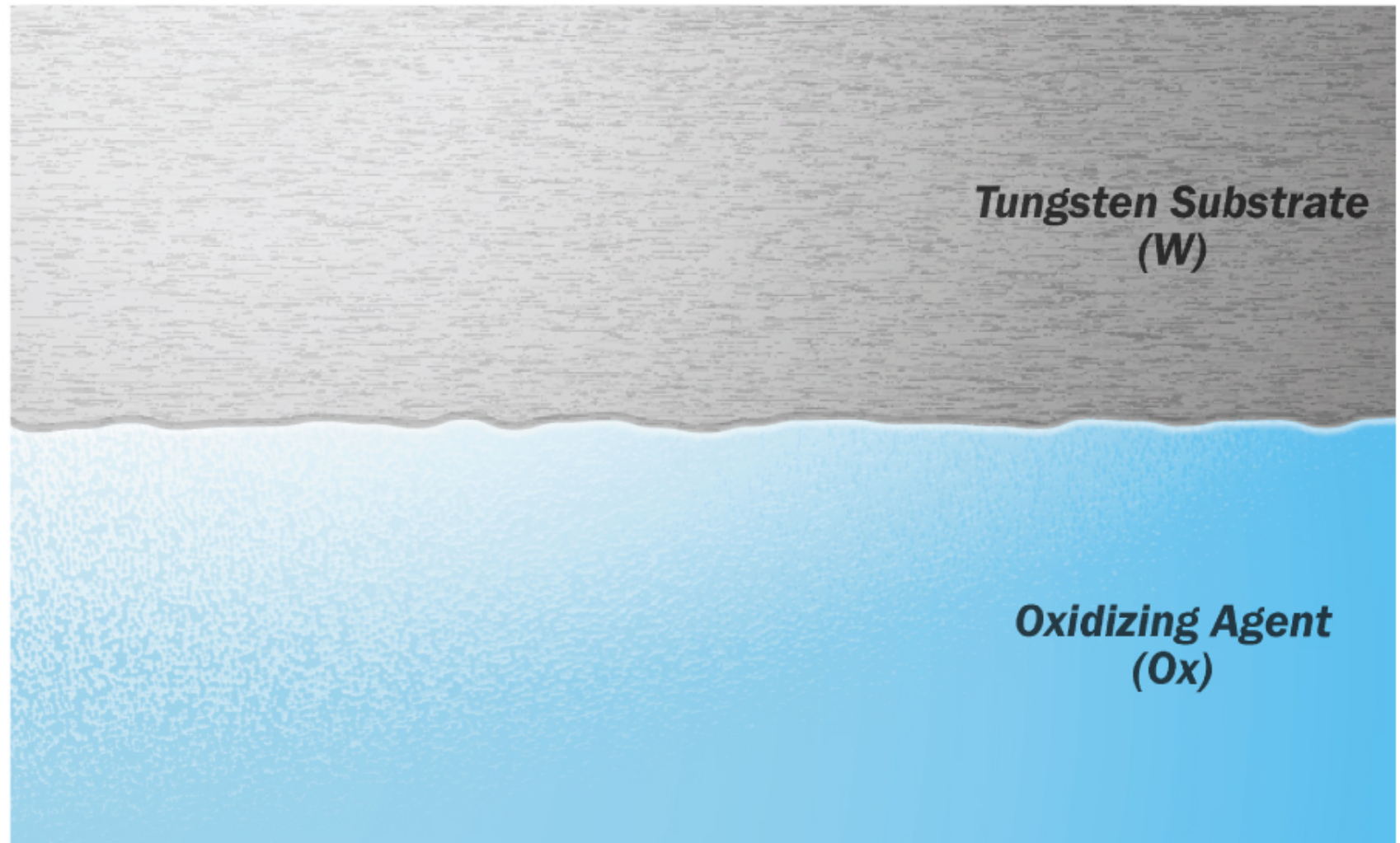
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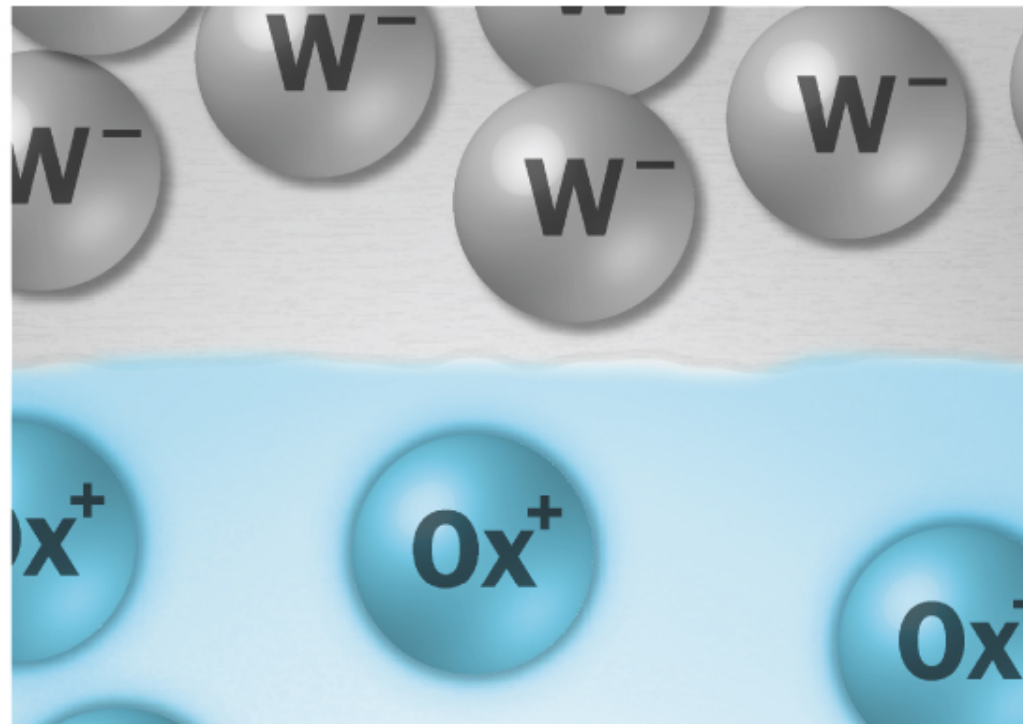
Oxidation of a Metal Surface

ELECTRONS ARE “SHUFFLED”

Oxidation of a Metal Surface — Electrons Are “Shuffled”



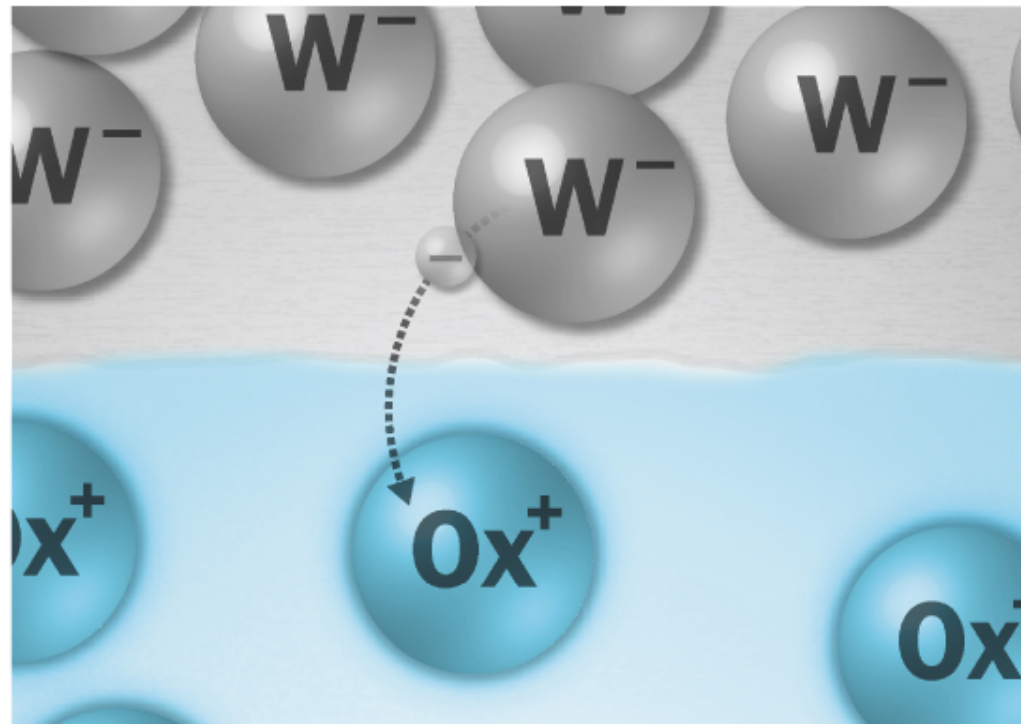
Oxidation of a Metal Surface — Electrons Are “Shuffled”



**Tungsten Substrate
(W)**

**Oxidizing Agent
(Ox)**

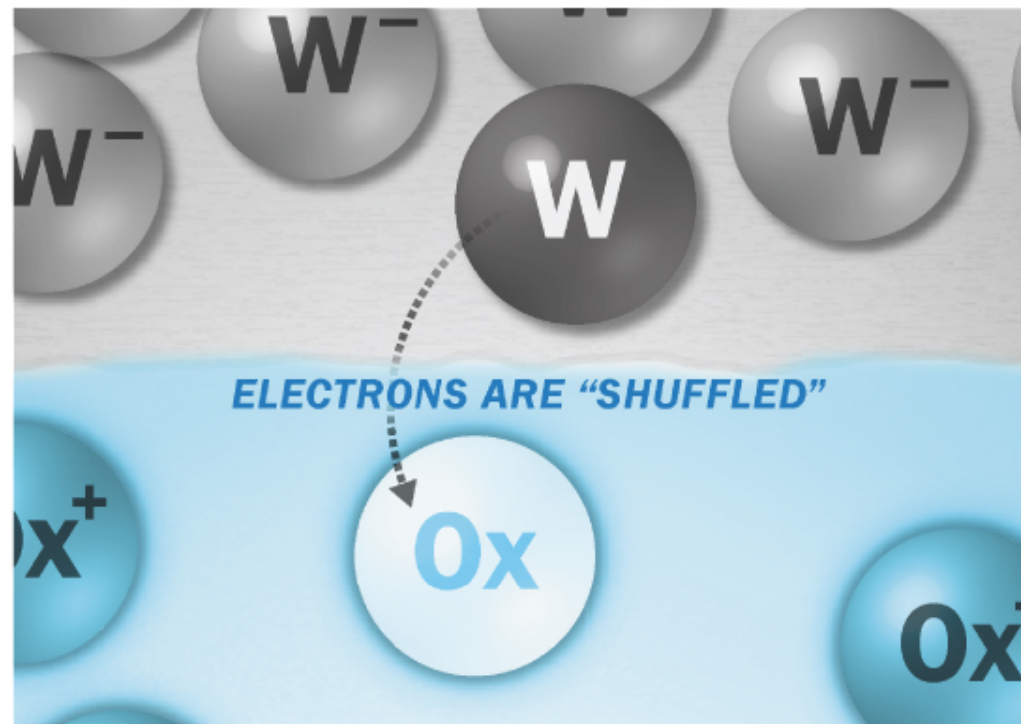
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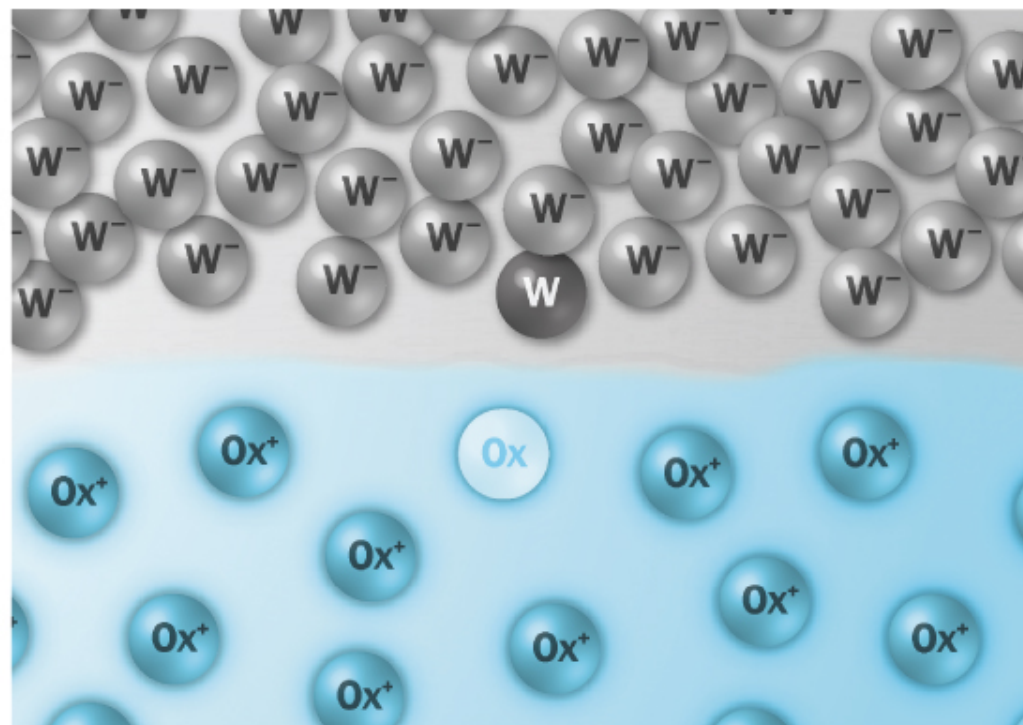
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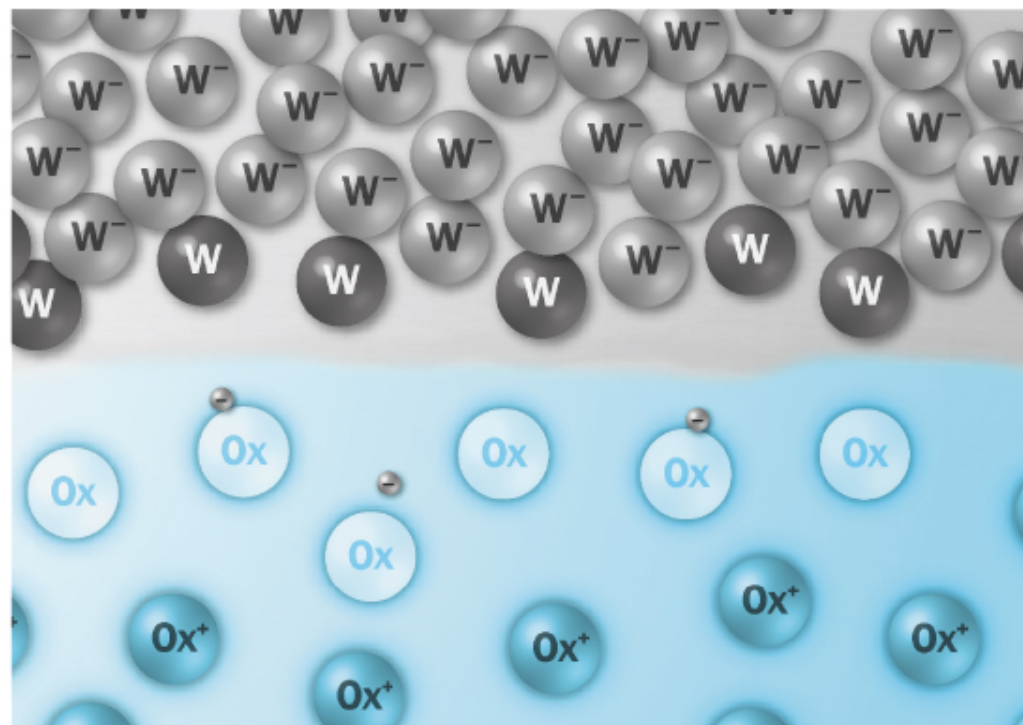
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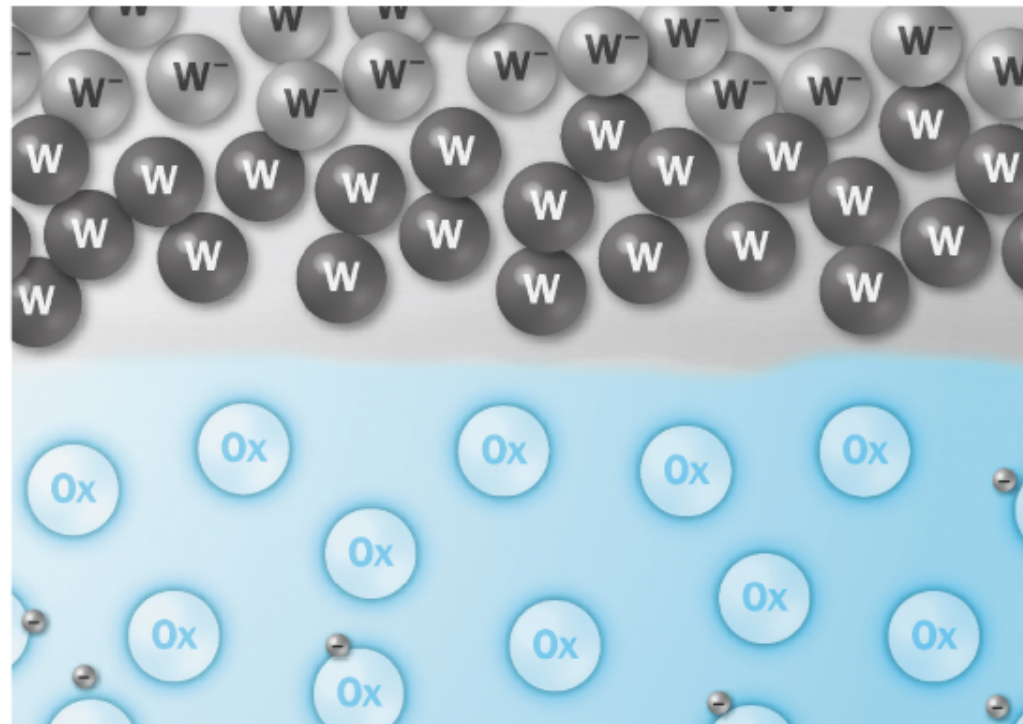
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